

LASER DIODE

NDL7515P Series

InGaAsP MQW DC-PBH PULSED LASER DIODE MODULE 1 310 nm OTDR APPLICATION

DESCRIPTION

The NDL7515P Series is a 1 310 nm newly developed Multiple Quantum Well (MQW) structure pulsed laser diode module with single mode fiber. It is designed for light source of optical measurement equipment (OTDR).

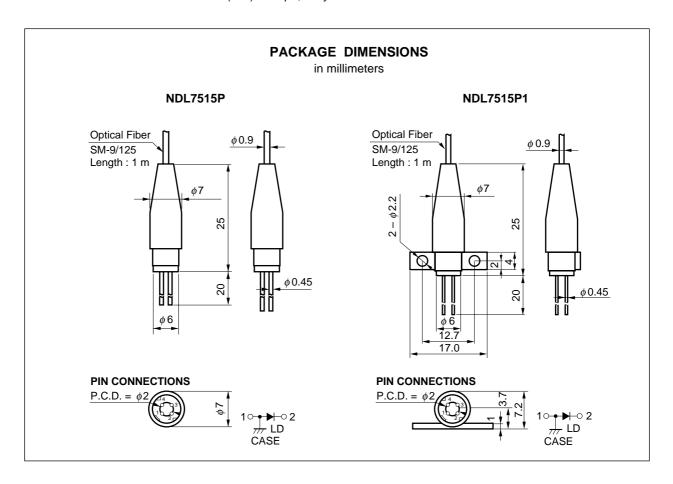
FEATURES

• Output power $P_f = 20 \text{ mW MIN.} @ I_{FP} = 400 \text{ mA}, T_C = 25 ° C^{-1}$

• Long wavelength $\lambda c = 1 \ 310 \ nm$ • Coaxial module without thermoelectric cooler

· Single mode fiber pigtail

*1 Pulse conditions: Pulse width (PW) = 10 μ s, Duty = 1 %



The information in this document is subject to change without notice.



ORDERING INFORMATION

| Part Number | Available Connector | Flange Type |
|-------------|----------------------|-------------------|
| NDL7515P | Without Connector | No Flange |
| NDL7515PC | With FC-PC Connector | |
| NDL7515P1 | Without Connector | Flat Mount Flange |
| NDL7515P1C | With FC-PC Connector | |

ABSOLUTE MAXIMUM RATINGS (Tc = 25 °C, unless otherwise specified)

| Parameter | Symbol | Ratings | Unit |
|-------------------------------------|------------------|------------|------|
| Pulsed Forward Current [™] | IFP | 600 | mA |
| Reverse Voltage of LD | VR | 2.0 | V |
| Operating Case Temperature | Tc | −20 to +60 | °C |
| Storage Temperature | T _{stg} | -40 to +85 | °C |
| Lead Soldering Temperature (10 s) | T _{sld} | 260 | °C |

^{*1} Pulse conditions: Pulse width (PW) = 10 μ s, Duty = 1 %

ELECTRO-OPTICAL CHARACTERISTICS (Tc = 25 °C)

| Parameter | Symbol | Conditions | MIN. | TYP. | MAX. | Unit |
|---------------------------------|--------|---|-------|-------|-------|------|
| Forward Voltage | VFP | I _{FP} = 400 mA, PW = 10 μs, Duty = 1 % | | 2.5 | 4.0 | V |
| Threshold Current | Ith | | | 20 | 30 | mA |
| Optical Output Power from Fiber | Pf | I _{FP} = 400 mA, PW = 10 μs, Duty = 1 % | 20 | 30 | | mW |
| Center Wavelength | λς | I _{FP} = 400 mA, PW = 10 μs, Duty = 1 %, RMS (–20 dB) | 1 290 | 1 310 | 1 330 | nm |
| Spectral Width | σ | I _{FP} = 400 mA, PW = 10 μs, Duty = 1 %, RMS (–20 dB) | | | 10 | nm |
| Rise Time | tr | 10 to 90 % | | | 1.0 | ns |
| Fall Time | tf | 90 to 10 % | | | 1.0 | ns |

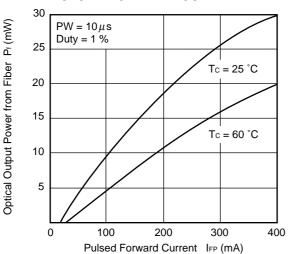
ELECTRO-OPTICAL CHARACTERISTICS (Tc = 0 to +60°C)

| Parameter | Symbol | Conditions | MIN. | TYP. | MAX. | Unit |
|--|--------|--|-------|------|---------|-------|
| Threshold Current | Ith | | | | 50 | mA |
| Optical Output Power from Fiber | Pf | I _{FP} = 400 mA, PW = 10 μs, Duty = 1 % | 10 | | | mW |
| Center Wavelength | λο | $I_{FP} = 400 \text{ mA}, PW = 10 \mu \text{s},$ Duty = 1 %, RMS (-20 dB) | 1 280 | | 1 342.5 | nm |
| Temperature Dependence of Center Wavelength | Δλ/ΔΤ | | | 0.35 | | nm/°C |
| Spectral Width | σ | I _{FP} = 400 mA, PW = 10 μs, Duty = 1 %, RMS (–20 dB) | | | 10 | nm |

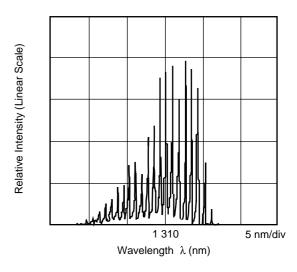
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★ TYPICAL CHARACTERISTICS (Tc = 25 °C, unless otherwise specified)

OPTICAL OUTPUT POWER FROM FIBER vs. LD PULSED FORWARD CURRENT



LONGITUDINAL MODE (FROM FIBER)



★ LASER DIODE FAMILY FOR OTDR APPLICATION

| Features | 1.31 μ | m | 1.55 μ | m | l _{FP} *1 | |
|----------------------------|-------------|---------------------|-------------|---------------------|--------------------|-----------------|
| Packages | Part Number | P (mW) MIN./TYP. | Part Number | P (mW) MIN./TYP. | (mA) | Remarks |
| φ 5.6 Can | NDL7103 | 290/320 | NDL7153 | 220/240 | 1 000 | |
| | NDL7113 | 160/175 | NDL7163 | 100/120 | 400 | |
| 4-pin Coaxial Module with | NDL7503P/P1 | 110/180 | NDL7553P/P1 | 95/145 | 1 000 | P : No flange |
| SMF | NDL7513P/P1 | 70/110 | NDL7563P/P1 | 60/80 | 400 | P1: With flange |
| | NDL7514P/P1 | 25/50 | NDL7564P/P1 | 20/40 | 400 | |
| | NDL7515P/P1 | 20/30 | NDL7565P/P1 | 8/11 | 400 | |
| 14-pin DIP Module with SMF | NDL7502P | 125/190 | NDL7552P | 100/125 | 1 000 | With TEC and |
| | NDL7512P | 90/110 | NDL7562P | 70/80 | 400 | Thermistor |
| | NDL7510P | 40/55 | NDL7560P | 20/30 | 400 | |

^{*1} Pulse conditions: Pulse width = 10 μ s, Duty = 1 % (modules)

Pulse width = 1 μ s, Duty = 1 % (ϕ 5.6 can)



REFERENCE

| Document Name | Document No. | | |
|---|--------------|--|--|
| NEC semiconductor device reliability/quality control system | LEI-1201 | | |
| Quality grades on NEC semiconductor devices | C11531E | | |
| Semiconductor device mounting technology manual | C10535E | | |
| Guide to quality assurance for semiconductor devices | MEI-1202 | | |
| Semiconductor selection guide | X10679E | | |

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[MEMO]

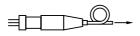
[MEMO]

CAUTION

Within this device there exists GaAs (Gallium Arsenide) material which is a harmful substance if ingested. Please do not under any circumstances break the hermetic seal.



SEMICONDUCTOR LASER



AVOID EXPOSURE-Invisible Laser Radiation is emitted from this aperture NEC Corporation NEC Building, 7-1, Shiba 5-chome, Minato-ku, Tokyo 108-01, Japan

Type number: ___

Serial Number:

This product conforms to FDA regulations as applicable to standards 21 CFR Chapter 1. Subchapter J.

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NEC devices are classified into the following three quality grades:

"Standard", "Special", and "Specific". The Specific quality grade applies only to devices developed based on a customer designated "quality assurance program" for a specific application. The recommended applications of a device depend on its quality grade, as indicated below. Customers must check the quality grade of each device before using it in a particular application.

Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic

equipment and industrial robots

Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed

for life support)

Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

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Anti-radioactive design is not implemented in this product.

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